



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23 Plastic-Encapsulate Diodes

BAS21/A/C/SLT1 SWITCHING DIODE

FEATURES

Power dissipation

P_D : 225 mW ($T_{amb}=25^{\circ}C$)

Forward Current

I_F : 200 mA

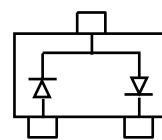
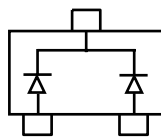
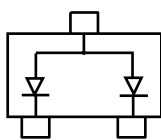
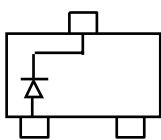
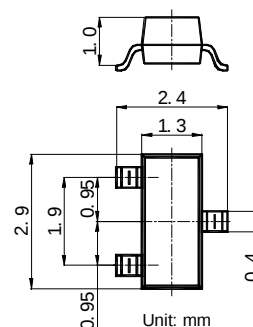
Reverse Voltage

V_R : 250 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-23



BAS21LT1

Marking: JS

BAS21ALT1

Marking: JS2

BAS21CLT1

Marking: JS3

BAS21SLT1

Marking: JS4

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	250		V
Reverse voltage leakage current	I_R	$V_R=200V$		1	μA
Forward voltage	V_F	$I_F=100mA$ $I_F=200mA$		1000 1250	mV
Diode capacitance	C_D	$V_R=0V, f=1MHz$		5	pF
Reverse recovery time	t_{rr}			50	nS